Docket No. MI22-2271

## ABSTRACT OF THE DISCLOSURE

A method of etching silicon nitride substantially selectively relative to an oxide of aluminum includes providing a substrate comprising silicon nitride and an oxide of aluminum. The silicon nitride and the oxide is exposed to an etching solution comprising HF and an organic HF solvent under conditions effective to etch the silicon nitride substantially selectively relative to the oxide. Other aspects and implementations are contemplated.

MI22\2271\P02.doc 25